





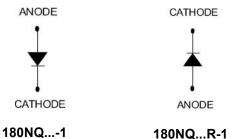
180NQ035/R-1 180NQ040/R-1 180NQ045/R-1 SCHOTTKY RECTIFIER



Features

- 150 ℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5' S
- Easier to mount and lower profile than DO-5' S
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Baseplate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- **Reverse battery protection**

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V_{RRM}	-	35	180NQ035(R)-1	
Working Peak Reverse Voltage	V _{RWM}		40 180NQ040(R)-1		V
DC Blocking Voltage	V_R		45	180NQ045(R)-1	
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =90°C, rectangular wave form	180		А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse		3480	Α
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25℃,I _{AS} =36A,L=0.37mH	243		mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T_J max. V_A =1.5 $\times V_R$ typical	36		А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 180A, Pulse, T _J = 25 °C	0.58	0.60	V
	VFI	@ 360A, Pulse, T _J = 25 °C	-	0.78	V
	\/	@ 180A, Pulse, T _J = 125 °C	0.50	0.56	V
	V_{F2}	@ 360A, Pulse, T _J = 125 °C	-	0.75	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	0.3	15	mA
	I _{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	250	600	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C	5800	7700	pF
		f _{SIG} = 1MHz	5500	7.700	Pi
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specific	Units	
Junction Temperature	TJ	-	-55 to +150		°C
Storage Temperature	T _{stg}	-	-55 to +150		°C
Typical Thermal Resistance Junction to Case	R _θ JC	DC operation	0.30		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.15		°C/W
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm
Approximate Weight	wt	-	25.6		g
Case Style	PRM1-1				

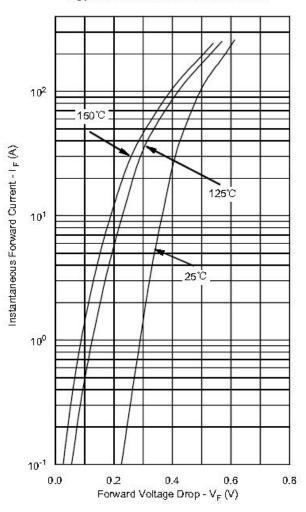




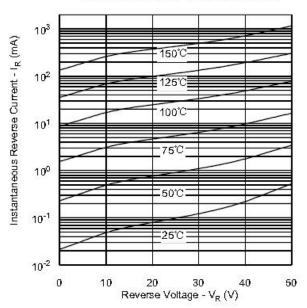


Ratings and Characteristics Curves

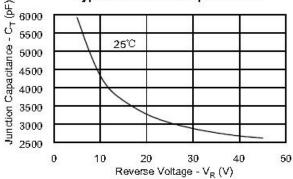
Typical Forward Characteristics



Typical Reverse Characteristics





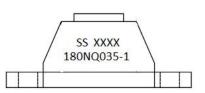


Ordering Information

Device Package		Shipping	
180NQ SERIES	PRM1-1(Pb-Free)	27pcs/ box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXX is YYWW

1st row SS YYWW 2nd row 180NQ035-1 SS = SS = Year ww = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

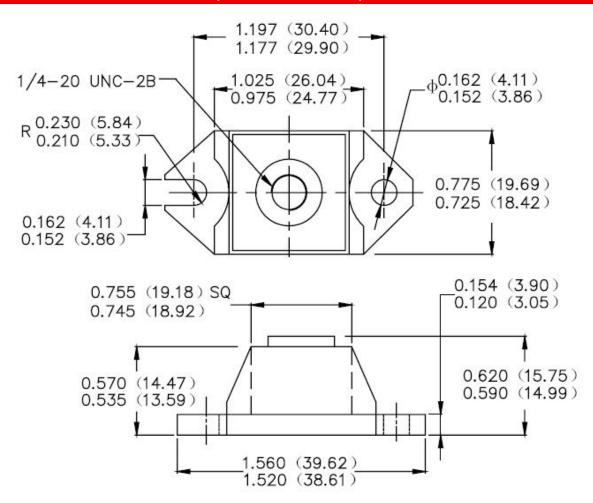
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Mechanical Dimensions PRM1-1 (Inches/Millimeters)



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